

# Jusang

## List of Publications by Year in descending order

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Version: 2024-02-01

21  
papers

1,357  
citations

516215

16  
h-index

713013

21  
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21  
all docs

21  
docs citations

21  
times ranked

2654  
citing authors

#	ARTICLE	IF	CITATIONS
1	Controllable synthesis of molybdenum tungsten disulfide alloy for vertically composition-controlled multilayer. <i>Nature Communications</i> , 2015, 6, 7817.	5.8	188
2	Exciton dynamics in atomically thin MoS <sub>2</sub> : Interexcitonic interaction and broadening kinetics. <i>Physical Review B</i> , 2013, 88, .	1.1	173
3	Synthesis of carbon nanotube/nickel nanocomposites using atomic layer deposition for high-performance non-enzymatic glucose sensing. <i>Biosensors and Bioelectronics</i> , 2015, 63, 325-330.	5.3	150
4	Improved Sensitivity in Schottky Contacted Two-Dimensional MoS <sub>2</sub> Gas Sensor. <i>ACS Applied Materials &amp; Interfaces</i> , 2019, 11, 38902-38909.	4.0	117
5	Recovery Improvement for Large-Area Tungsten Diselenide Gas Sensors. <i>ACS Applied Materials &amp; Interfaces</i> , 2018, 10, 23910-23917.	4.0	115
6	2D Transition Metal Dichalcogenide Heterostructures for p- and n-Type Photovoltaic Self-Powered Gas Sensor. <i>Advanced Functional Materials</i> , 2020, 30, 2003360.	7.8	102
7	High-Performance Gas Sensor Using a Large-Area WS <sub>2</sub> /Se <sub>2</sub> Alloy for Low-Power Operation Wearable Applications. <i>ACS Applied Materials &amp; Interfaces</i> , 2018, 10, 34163-34171.	4.0	93
8	Layer-modulated synthesis of uniform tungsten disulfide nanosheet using gas-phase precursors. <i>Nanoscale</i> , 2015, 7, 1308-1313.	2.8	86
9	Self-Limiting Layer Synthesis of Transition Metal Dichalcogenides. <i>Scientific Reports</i> , 2016, 6, 18754.	1.6	74
10	Atomic layer deposition of Y <sub>2</sub> O <sub>3</sub> and yttrium-doped HfO <sub>2</sub> using a newly synthesized Y(iPrCp) <sub>2</sub> (N-iPr-amd) precursor for a high permittivity gate dielectric. <i>Applied Surface Science</i> , 2014, 297, 16-21.	3.1	54
11	Atomic Layer Deposition-Based 2D Transition Metal Chalcogenides: Synthesis, Modulation, and Applications. <i>Advanced Materials</i> , 2021, 33, e2005907.	11.1	42
12	Effect of Al <sub>2</sub> O <sub>3</sub> Deposition on Performance of Top-Gated Monolayer MoS <sub>2</sub> -Based Field Effect Transistor. <i>ACS Applied Materials &amp; Interfaces</i> , 2016, 8, 28130-28135.	4.0	40
13	n-ZnO/N/p-Si nanowire photodiode prepared by atomic layer deposition. <i>Applied Physics Letters</i> , 2012, 100, .	1.5	32
14	Plasma-enhanced atomic layer deposition of Co using Co(MeCp) <sub>2</sub> precursor. <i>Journal of Energy Chemistry</i> , 2013, 22, 403-407.	7.1	23
15	Nitrogen-doped ZnO/n-Si core-shell nanowire photodiode prepared by atomic layer deposition. <i>Materials Science in Semiconductor Processing</i> , 2015, 33, 154-160.	1.9	19
16	Synthesis and Application of AgBiS <sub>2</sub> and Ag <sub>2</sub> S Nanoinks for the Production of IR Photodetectors. <i>ACS Omega</i> , 2021, 6, 20710-20718.	1.6	19
17	Interface Defect Engineering of a Large-Scale CVD-Grown MoS <sub>2</sub> Monolayer via Residual Sodium at the SiO <sub>2</sub> /Si Substrate. <i>Advanced Materials Interfaces</i> , 2021, 8, 2100428.	1.9	14
18	Vapor Deposition Techniques for Synthesis of Two-Dimensional Transition Metal Dichalcogenides. <i>Applied Microscopy</i> , 2015, 45, 119-125.	0.8	7

#	ARTICLE	IF	CITATIONS
19	Photocurrent Enhancement of PtSe <sub>2</sub> Photodetectors by Using Au Nanorods. Photonics, 2021, 8, 505.	0.9	7
20	Self-Powered Gas Sensors: 2D Transition Metal Dichalcogenide Heterostructures for p- and n-Type Photovoltaic Self-Powered Gas Sensor (Adv. Funct. Mater. 43/2020). Advanced Functional Materials, 2020, 30, 2070284.	7.8	1
21	Interface Defect Engineering of MoS <sub>2</sub> Monolayer: Interface Defect Engineering of a Large-Scale CVD-Grown MoS <sub>2</sub> Monolayer via Residual Sodium at the SiO <sub>2</sub> /Si Substrate (Adv. Mater. Interfaces 14/2021). Advanced Materials Interfaces, 2021, 8, 2170080.	1.9	1